5 é / Descriptions

SOT-23 .> / / x N 3 MOS « | • ’ož

4- CHANNEL MOSFET in a SOT-23 Plastic Package.

¤ ª / Features

V_{DS} (V) = 30V

I_D = 5.5 A (V_{GS} = 20V)

$R_{DS(ON)}$ < 31m (VGS = 10V)

$R_{DS(ON)}$ < 43m (VGS = 4.5V)

—)í D }ož HF Product.

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This device is suitable for use as a load switch or in PWM applications.

Ã W] Ô · / Equivalent Circuit

PIN1 y G PIN 2 y S PIN 3 y D

, M V / Marking

@ *f* Parameter		… Z Symbol	*f* › Rating	% y Unit
Drain-Source Voltage		V_{DS}	30	V
Drain Current – Continuous		I_D	5.5	A
Pulsed Drain Current		I_{DM}	19	A
Gate-Source Voltage		V_{GS}	±20	V
Total Power Dissipation		P_D	1.4	W
Operating and Storage Junction Temperature Range		T_J, T_{STG}	-55 to 150	
Maximum Junction-to-Ambient	t 0 10s	$R_{\theta JA}$	90	/W
Maximum Junction-to-Ambient	Steady-State		125	
		$R_{\theta JL}$	80	

@ *f*	… Z	Symbol			
Parameter	Symbol	Unit	I	m	- .

Ô ? d • Ž ¢ / Electrical Characteristic Curve

Ô ? d • Ž ¢ / Electrical Characteristic Curve

Ø ¤ =) ¢ / Package Dimensions

, M y ƒ / Marking Instructions

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š WD t … • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½180 - k ž • 60 ½90sec;

2o• Q › “ † 245 r 5 - k ž • 4 Ò 5 r 0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~180 - , Time:60~90sec.

2.Peak Temp.:245 r 5 - , Duration:5 r 0.5sec.

3. Cooling Speed: 2~10 - /sec.